

## ABSTRACT OF THE DISCLOSURE

A ZnSe based light emitting device enabling longer lifetime is provided. The light emitting device is formed on a compound semiconductor, includes an active layer positioned between an n-type ZnMgSSe cladding layer and a p-type ZnMgSSe cladding layer, and has a barrier layer having a band gap larger than that of the p-type ZnMgSSe cladding layer, provided between the active layer and the p-type ZnMgSSe cladding layer.

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